

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claims 1-17 (Canceled).

18. (Currently Amended) A method of producing a semiconductor device according to Claim ~~17~~24,

wherein the plurality of the contact terminals are pyramidal or truncated pyramidal.

19. (Currently Amended) A method of producing a semiconductor device according to Claim ~~17~~24,

wherein the plurality of the contact terminals are formed using, as a mold member, the holes formed by anisotropic etching of a crystalline board.

Claim 20 (Canceled).

21. (Currently Amended) A method of producing a semiconductor device according to Claim ~~20~~27,

wherein the probe card further includes a means for applying pressure to an area formed with the first metal film and an area formed with the plurality of the contact terminals of the probe sheet, and

wherein the electrical characteristics of each semiconductor element

are tested by the pressure application means applying pressure to the area formed with the first metal film and the area formed with the plurality of the contact terminals of the probe sheet while making the plurality of the contact terminals in contact with the electrodes of the semiconductor element.

22. (Currently Amended) A method of producing a semiconductor device according to Claim 2027,

wherein the plurality of the contact terminals are pyramidal or truncated pyramidal.

23. (Currently Amended) A method of producing a semiconductor device according to Claim 2027,

wherein the plurality of the contact terminals are formed using, as a mold member, the holes formed by anisotropic etching of a crystalline board.

24. (New) A method of producing a semiconductor device, comprising the steps of:

building a circuit in a wafer and forming a plurality of semiconductor elements;

contacting a plurality of contact terminals formed within a first area surrounded by a first metal film of a probe sheet to each of a plurality of electrodes provided at the semiconductor elements to test electrical characteristics of each of the semiconductor elements; and

dicing and separating the wafer into the semiconductor elements;

wherein the electrical characteristics of each of the semiconductor elements are tested by pushing the first area surrounded by the first metal film while fixing a second metal film formed so as to surround the first metal film of the probe sheet thereby to make the plurality of the contact terminals contact with the

electrodes of the semiconductor element to perform the testing.

25. (New) A method of producing a semiconductor device according to claim 24, wherein the first metal film has a linear expansion coefficient substantially the same as a linear expansion coefficient of the wafer.

26. (New) A method of producing a semiconductor device according to claim 25, wherein the first metal film is formed by 42 alloy or invar.

27. (New) A method of producing a semiconductor device, comprising the steps of:

building a circuit in a wafer and forming a plurality of semiconductor elements;

contacting a plurality of contact terminals formed within a first area surrounded by a first metal film of a probe card having a probe sheet to each of a plurality of electrodes provided at the semiconductor elements to test electrical characteristics of each of the semiconductor elements; and

dicing and separating the wafer into the semiconductor elements;

wherein the electrical characteristics of each of the semiconductor elements are tested by pushing the first area surrounded by the first metal film while fixing a second metal film formed so as to surround the first metal film of the probe sheet thereby to make the plurality of the contact terminals contact with the electrodes of the semiconductor element to perform the testing.

28. (New) A method of producing a semiconductor device according to claim 27, wherein the first metal film has a linear expansion coefficient substantially the same as a linear expansion coefficient of the wafer.

29. (New) A method of producing a semiconductor device according to claim 28,
wherein the first metal film is formed by 42 alloy or invar